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ZXTN19100CZ

100V NPN medium power transistor in SOT89

Summary

BV_{CEX} > 200V

BV_{CEO} > 100V

 $BV_{ECO} > 5V$

 $I_{C(cont)} = 5.25A$

V_{CE(sat)} < 65mV @ 1A

 $R_{CE(sat)} = 44m\Omega$

 $P_D = 2.4W$



Complementary part number ZXTP19100CZ

Description

Packaged in the SOT89 outline this new low saturation NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

Features

- Higher power dissipation SOT89 package
- · High peak current
- · Low saturation voltage
- · High forward blocking voltage

Applications

- · PSU start up switch
- Motor drive
- · Lamp, relay and solenoid switches

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN19100CZTA	7	12	1000

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Pinout - top view

Device marking

1L9

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V _{CBO}	200	V
Collector-Emitter voltage (forward blocking)	V _{CEX}	200	V
Collector-Emitter voltage	V _{CEO}	100	V
Emitter-Collector voltage (reverse blocking)	V _{ECX}	6	V
Emitter-Base voltage	V _{EBO}	7	V
Continuous Collector current ^(c)	Ic	5.25	Α
Base current	I _B	1	Α
Peak pulse current	I _{CM}	10	Α
Power dissipation at T _A =25°C ^(a)	P _D	1.1	W
Linear derating factor		8.8	mW/°C
Power dissipation at T _A =25°C ^(b)	P _D	1.8	W
Linear derating factor		14.4	mW/°C
Power dissipation at T _A =25°C ^(c)	P _D	2.4	W
Linear derating factor		19.2	mW/°C
Power dissipation at T _A =25°C ^(d)	P _D	4.46	W
Linear derating factor		35.7	mW/°C
Power dissipation at T _C =25°C ^(e)	P _D	26.6	W
Linear derating factor		213	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	117	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	68	°C/W
Junction to ambient ^(c)	$R_{\Theta JA}$	51	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	28	°C/W
Junction to case ^(e)	$R_{\Theta JC}$	4.69	°C/W

NOTES:

⁽a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

⁽b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

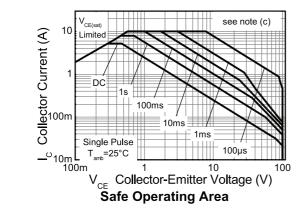
⁽c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

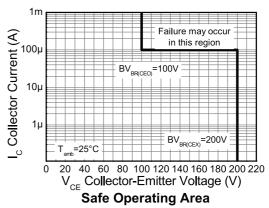
⁽d) As (c) above measured at t<5 seconds.

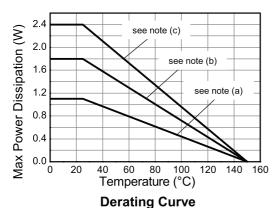
⁽e) Junction to case (collector tab). Typical.

ZXTN19100CZ

Thermal characteristics

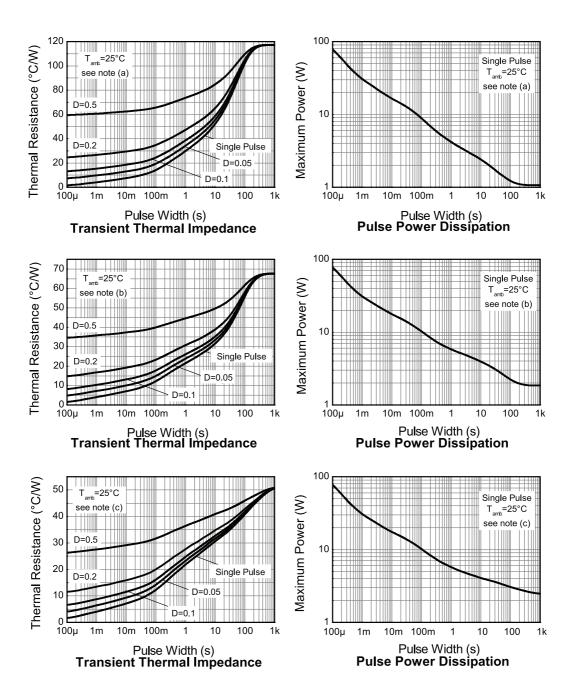






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Thermal characteristics



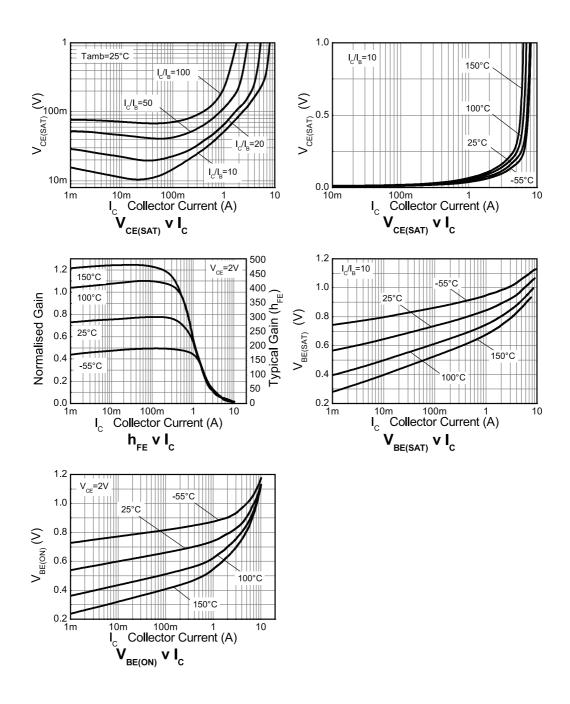
Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated).

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV _{CBO}	200	240		V	I _C = 100μA
Collector-Emitter breakdown voltage (forward blocking)	BV _{CEX}	200	240		V	I_C = 100μA, $R_{BE} \le 1$ k Ω or -1V < V _{BE} < 0.25V
Collector-Emitter breakdown voltage	BV _{CEO}	100	120		V	I _C = 10mA (*)
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECX}	6	8.3		V	$\begin{aligned} I_E &= 100 \mu A, \ R_{BC} \leq 1 k \Omega \ or \\ 0.25 V &> V_{BC} > -0.25 V \end{aligned}$
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECO}	5	8		V	I _E = 100μA
Emitter-Base breakdown voltage	BV _{EBO}	7	8.3		V	I _E = 100μA
Collector-Base cut-off	I _{CBO}		<1	50	nA	V _{CB} = 200V
current				0.5	μΑ	$V_{CB} = 200V, T_{amb} = 100^{\circ}C$
Collector-Emitter cut-off current	I _{CEX}			100	nA	V_{CE} = 200V, $R_{BE} \le 1k\Omega$ or -1V < V_{BE} < 0.25V
Emitter cut-off current	I _{EBO}		<1	50	nA	V _{EB} = 5.6V
Collector-Emitter	V _{CE(sat)}		50	65	mV	$I_C = 1A$, $I_B = 100 \text{mA}^{(*)}$
saturation voltage	5 = (5 3.1)		105	140	mV	$I_C = 1A$, $I_B = 20mA^{(*)}$
			210	350	mV	$I_C = 5.25A$, $I_B = 525mA^{(*)}$
Base-Emitter saturation voltage	V _{BE(sat)}		1000	1075	mV	$I_C = 5.25A$, $I_B = 525mA^{(*)}$
Base-Emitter turn-on voltage	V _{BE(on)}		930	1025	mV	$I_C = 5.25A, V_{CE} = 2V^{(*)}$
Static forward current transfer ratio	h _{FE}	200 130	300 200	500		I _C = 100mA, V _{CE} = 2V ^(*) I _C = 1A, V _{CE} = 2V ^(*)
			30			$I_C = 5.25A, V_{CE} = 2V^{(*)}$
Transition frequency	f _T		150		MHz	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}$ f = 100MHz
Input capacitance	C _{ibo}		305	400	pF	$V_{EB} = 0.5V, f = 1MHz^{(*)}$
Output capacitance	C _{obo}		15.7	25	pF	V _{CB} = 10V, f = 1MHz ^(*)
Delay time	t _d		28.3		ns	
Rise time	t _r		23.6		ns	$I_C = 500 \text{mA}, V_{CC} = 10 \text{V},$
Storage time	t _s		962		ns	$I_{B1} = -I_{B2} = 50 \text{mA}$
Fall time	t _f		133		ns	

NOTES:

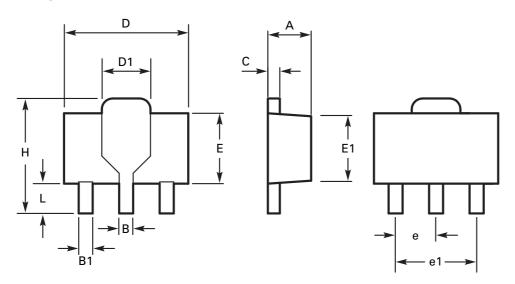
(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$

Typical characteristics



ZXTN19100CZ

Package outline - SOT89



DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	Е	2.29	2.60	0.090	0.102
В	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	е	1.50 BSC		0.059 BSC	
С	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118	BSC
D	4.40	4.60	0.173	0.181	Н	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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